



## N-Channel Enhancement-Mode Vertical DMOS FETs

### Ordering Information

$BV_{DSS} /$ $BV_{DGS}$	$R_{DS(ON)}$ (max)	$I_{D(ON)}$ (min)	Order Number / Package
			Die
500V	60Ω	150mA	VN1550NW

\* Die in wafer form.

### Features

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Low  $C_{ISS}$  and fast switching speeds
- Excellent thermal stability
- Integral Source-Drain diode
- High input impedance and high gain
- Complementary N- and P-channel devices

### Applications

- Motor controls
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

### Absolute Maximum Ratings

Drain-to-Source Voltage	$BV_{DSS}$
Drain-to-Gate Voltage	$BV_{DGS}$
Gate-to-Source Voltage	± 20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

\* Distance of 1.6 mm from case for 10 seconds.

### Advanced DMOS Technology

These enhancement-mode (normally-off) transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

## Electrical Characteristics (@ 25°C unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Unit	Conditions
$BV_{DSS}$	Drain-to-Source Breakdown Voltage	500			V	$V_{GS} = 0V, I_D = 1mA$
$V_{GS(th)}$	Gate Threshold Voltage	2		4	V	$V_{GS} = V_{DS}, I_D = 1mA$
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with Temperature		-3.8	-5.0	mV/°C	$V_{GS} = V_{DS}, I_D = 1mA$
$I_{GSS}$	Gate Body Leakage			100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
$I_{DSS}$	Zero Gate Voltage Drain Current			10	$\mu A$	$V_{GS} = 0V, V_{DS} = \text{Max Rating}$
				1	mA	$V_{GS} = 0V, V_{DS} = 0.8 \text{ Max Rating}$ $T_A = 125^\circ C$
$I_{D(ON)}$	ON-State Drain Current		100		mA	$V_{GS} = 5V, V_{DS} = 25V$
		150	350			$V_{GS} = 10V, V_{DS} = 25V$
$R_{DS(ON)}$	Static Drain-to-Source ON-State Resistance		45		$\Omega$	$V_{GS} = 5V, I_D = 50mA$
			40	60		$V_{GS} = 10V, I_D = 50mA$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with Temperature		1	1.7	%/°C	$V_{GS} = 10V, I_D = 50mA$
$G_{FS}$	Forward Transconductance	50	100		mS	$V_{DS} = 25V, I_D = 50mA$
$C_{ISS}$	Input Capacitance		45	55	pF	$V_{GS} = 0V, V_{DS} = 25V$ $f = 1 \text{ MHz}$
$C_{OSS}$	Common Source Output Capacitance		8	10		
$C_{RSS}$	Reverse Transfer Capacitance		2	5		
$t_{d(ON)}$	Turn-ON Delay Time			10	ns	$V_{DD} = 25V,$ $I_D = 150mA,$ $R_{GEN} = 25\Omega$
$t_r$	Rise Time			15		
$t_{d(OFF)}$	Turn-OFF Delay Time			10		
$t_f$	Fall Time			10		
$V_{SD}$	Diode Forward Voltage Drop		0.8		V	$V_{GS} = 0V, I_{SD} = 0.5A$
$t_{rr}$	Reverse Recovery Time		300		ns	$V_{GS} = 0V, I_{SD} = 0.5A$

### Notes:

- All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300 $\mu$ s pulse, 2% duty cycle.)
- All A.C. parameters sample tested.

## Switching Waveforms and Test Circuit

